No.2819A

SVC~~351~~,361

Diffused Junction Type Silicon Diode

Composite Varactor Diode for AM Receiver Electronic Tuning Use

Features

- Excellent matching characteristics because of composite type
- The number of manufacturing processes can be reduced and automatic mounting is possible because of composite type.
- High capacitance ratio and high quality factor

Absolute Maximum Ratings at Ta = 25°C

			unit
Reverse Voltage	V_R	−16	V
Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	−55 to +125	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Breakdown Voltage	$V_{(BR)R}$	I_R = −10μA	−16			V
Rerverse Current (One diode)	I_R	V_R = −9V			−100	nA
Interterminal Capacitance	C_{1V}	V_R = −1V, f = 1MHz*1	428.0※		500.0※	pF
(Average)	C_{6V}	V_R = −6V, f = 1MHz	48.0		65.0	pF
	C_{8V}	V_R = −8V, f = 1MHz	20.5		27.0	pF
Quality Factor	Q	V_R = −1V, f = 1MHz	200			
Capacitance Ratio	CR	C_{1V}/C_{8V}, f = 1MHz	16.5		23.5	
Matching Tolerance	ΔCm*2	V_R = −1 to −8V, f = 1MHz			±2.5	%

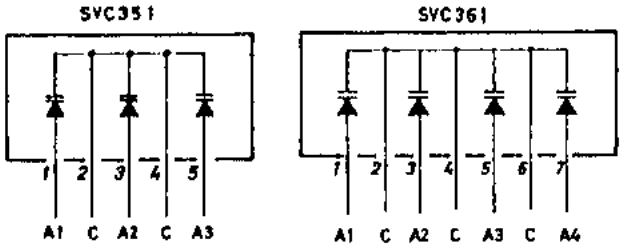
*1. 1MHz signal : 20mVrms

*2. $\Delta Cm = (C_{Dn} - C_{D3})/C_{D3} \times 100$

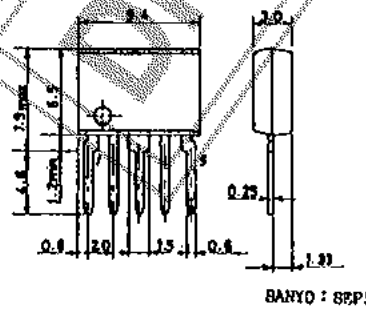
※ : The SVC351,361 are classified by C_{1V} as follows :

Rank	C_{1V} (pF)
K	428.0~456.5
L	447.5~478.0
M	468.5~500.0

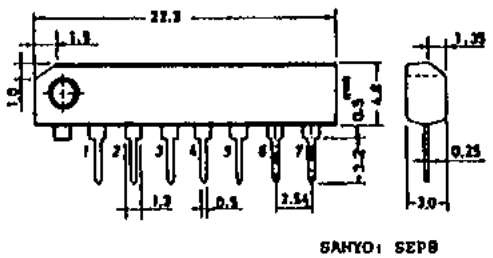
Electrical Connection



Case Outline 1194 [SVC361]
(unit : mm)



Case Outline 1204 [SVC361]
(unit : mm)



Specifications and information herein are subject to change without notice.

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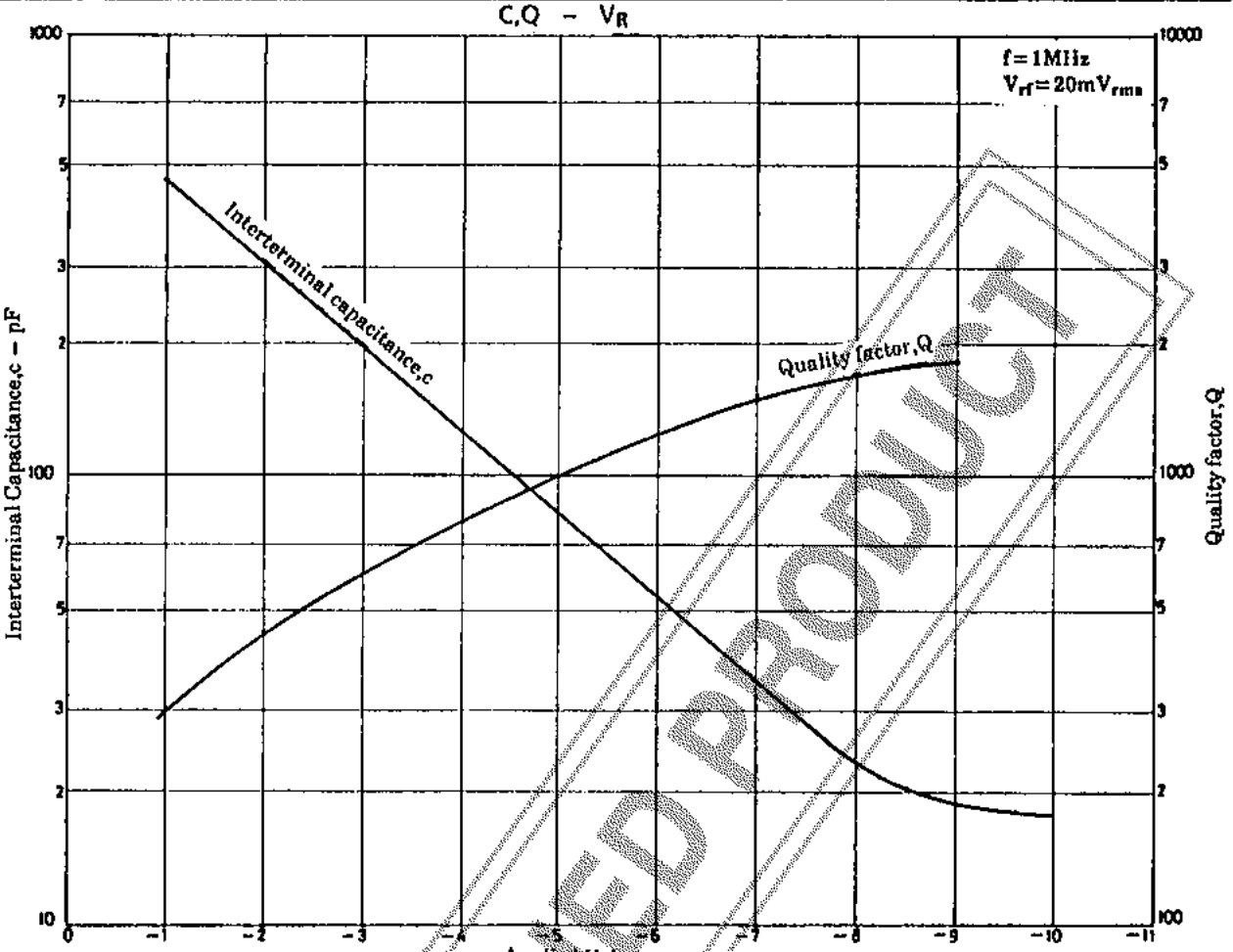
C,Q – V_R



C – T_a